

HORIZONTAL TRAM AND METHOD FOR THE FABRICATION THEREOF

ABSTRACT

A method for manufacturing an integrated circuit structure includes providing a semiconductor substrate and forming a trench therein. A thyristor is formed around the trench and within the semiconductor substrate. The thyristor has at least four layers with three P-N junctions therebetween. A gate for the thyristor is formed within the trench. An access transistor is formed on the semiconductor substrate. An interconnect is formed between the thyristor and the access transistor.

FIG. 9